Silicon PNP Power Transistors 2SA900

DESCRIPTION

·With TO-126 package
·Complement to type 2SC1568
·Low collector saturation voltage

APPLICATIONS

·For audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

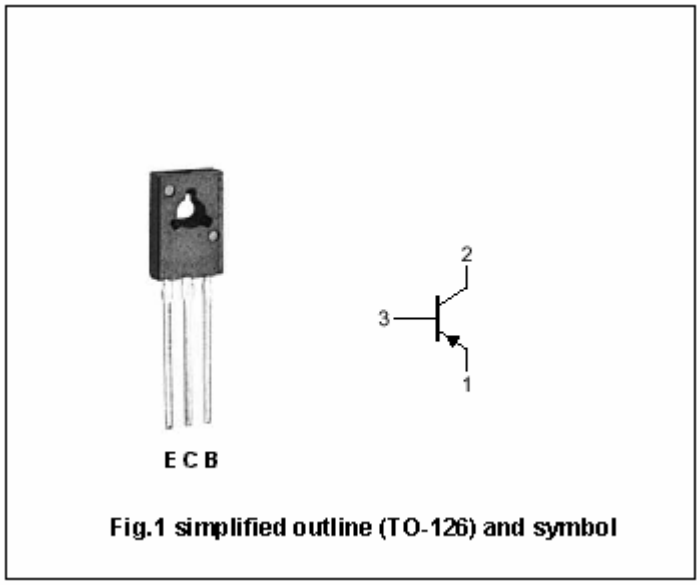

Fig.1 simplified outline (TO-126) and symbol

Absolute Maximun Ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-20	V
V_{CEO}	Collector-emitter voltage	Open base	-18	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
I_{CM}	Collector current-peak		-2	A
P_C	Collector power dissipation	T_C=25□	1.2	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA;I_B=0	-18			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-10μA ;I_E=0	-20			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-10μA ;I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1A ;I_B=-50mA			-0.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-500mA ;I_B=-50mA			-1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=-10V; I_E=0			-1	μA
I_{CEO}	Collector cut-off current	V_{CE}=-18V; I_B=0			-10	μA
h_{FE-1}	DC current gain	I_C=-500mA ; V_{CE}=-2V	90		470	
h_{FE-2}	DC current gain	I_C=-1.5A ; V_{CE}=-2V	50			
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-6V;f=1MHz		40		pF
f_T	Transition frequency	I_E=50mA ; V_{CB}=-6V		200		MHz

◆ **h_{FE-1} Classifications**

Q	R	S	T	U
90-155	130-210	180-280	250-360	330-470

PACKAGE OUTLINE

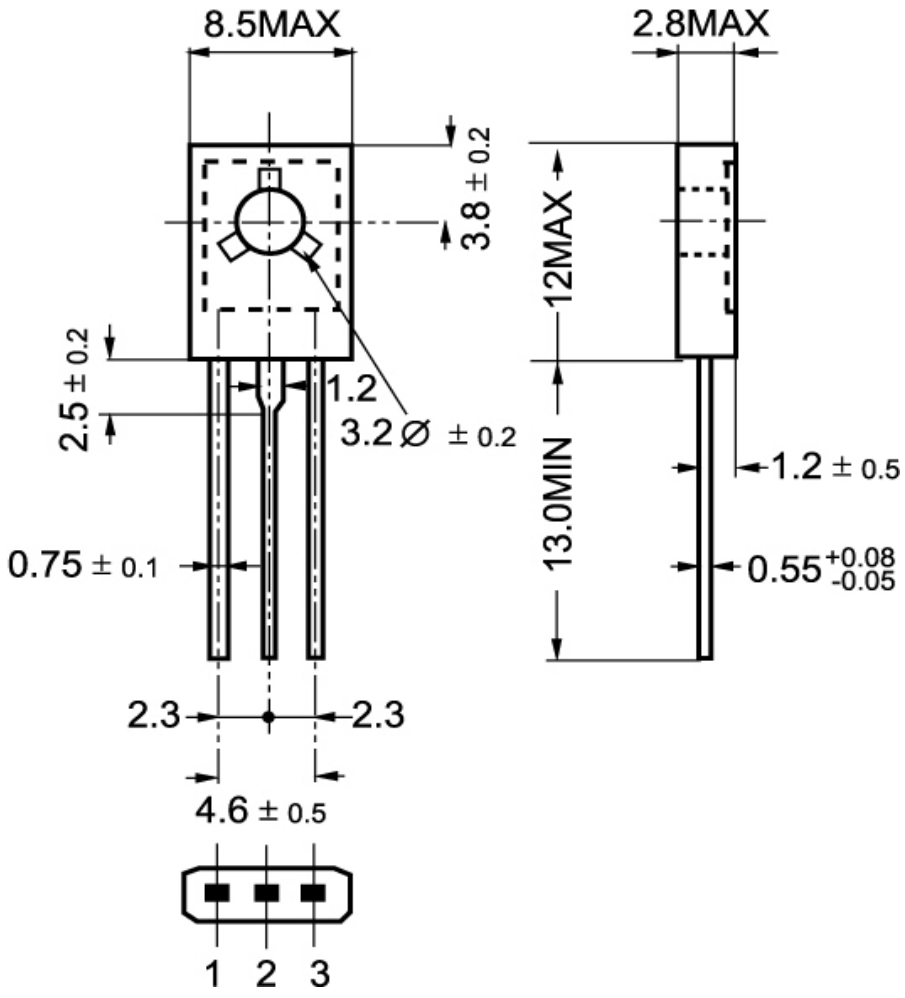

Fig.2 Outline dimensions